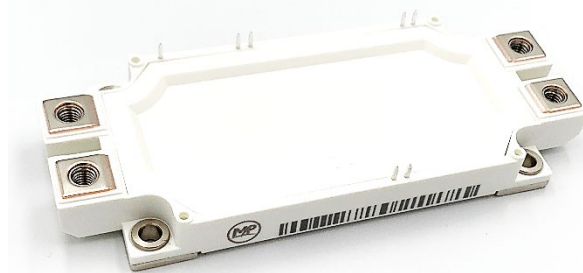


Electrical Features

- Trench/Fieldstop IGBT
- Low $V_{CE(sat)}$
- $V_{CE(sat)}$ with positive temperature coefficient
- 10 μ s short circuit capability
- Fast&soft reverse recovery anti-parallel FWD
- Low inductance case



Typical Applications

- Motor Drives
- UPS System
- Servo Drives
- Wind Turbines

IGBT, Inverter

Maximum Rated Values						
Symbol	Item	Conditions	Rating			Unit
IGBT						
V_{CES}	Collector-emitter voltage	$T_{vj}=25^{\circ}\text{C}$	1200			V
V_{GES}	Gate-emitter voltage	-	± 20			V
I_C	Collector current,DC	$T_C=100^{\circ}\text{C}, T_{vj}=175^{\circ}\text{C}$	450			A
I_{CRM}	Repetitive peak collector current	$t_p=1\text{ms}$	900			A
t_{SC}	Short circuit withstand time	$V_{GE}=15\text{V}, V_{CC}=600\text{V}, T_{vj}\leq 150^{\circ}\text{C}$	10			μs
P_{tot}	Total power dissipation	$T_C=25^{\circ}\text{C}, T_{vj}=175^{\circ}\text{C}$	2586			W
Characteristics Values						
Symbol	Item	Conditions	Values			Unit
IGBT			Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_{vj}=25^{\circ}\text{C}$	-	-	10	μA
I_{GES}	Gate leakage current	$V_{CE}=0\text{V}, V_{GE}=20\text{V}, T_{vj}=25^{\circ}\text{C}$	-	-	50	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=17.1\text{mA}, V_{CE}=V_{GE}, T_{vj}=25^{\circ}\text{C}$	5.2	5.8	6.4	V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=450\text{A}$ $V_{GE}=15\text{V}$ $T_{vj}=25^{\circ}\text{C}$	-	2.19	-	
		$T_{vj}=125^{\circ}\text{C}$	-	2.64	-	
		$T_{vj}=150^{\circ}\text{C}$	-	2.77	-	
C_{ies}	Input capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}$ $f=1\text{MHz}, T_{vj}=25^{\circ}\text{C}$	-	73.3	-	nF
C_{oes}	Output capacitance		-	2.79	-	
C_{res}	Reverse transfer capacitance		-	0.18	-	
Q_G	Gate charge	$V_{GE}=\pm 15\text{V}$	-	3250	-	nC
R_g	Internal gate resistance	$T_{vj}=25^{\circ}\text{C}$	-	0.33	-	Ω

$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V,$ $I_C=450A,$ $V_{GE}=\pm 15V,$ $R_{G(on)}=5.1\ \Omega,$ $R_{G(off)}=5.1\ \Omega,$ $L_{load}=100\mu H$	$T_{vj}=25^\circ C$	-	174	-	ns
			$T_{vj}=125^\circ C$	-	170	-	
			$T_{vj}=150^\circ C$	-	148	-	
t_r	Rise time		$T_{vj}=25^\circ C$	-	156	-	
			$T_{vj}=125^\circ C$	-	160	-	
			$T_{vj}=150^\circ C$	-	168	-	
$t_{d(off)}$	Turn-off delay time		$T_{vj}=25^\circ C$	-	608	-	
			$T_{vj}=125^\circ C$	-	684	-	
			$T_{vj}=150^\circ C$	-	698	-	
t_f	Fall time		$T_{vj}=25^\circ C$	-	98	-	
			$T_{vj}=125^\circ C$	-	172	-	
			$T_{vj}=150^\circ C$	-	194	-	
E_{on}	Turn-on energy (per pulse)	$T_{vj}=25^\circ C$	-	64.8	-	mJ	
		$T_{vj}=125^\circ C$	-	86.6	-		
		$T_{vj}=150^\circ C$	-	93.1	-		
E_{off}	Turn-off energy (per pulse)	$T_{vj}=25^\circ C$	-	46.9	-		
		$T_{vj}=125^\circ C$	-	56.9	-		
		$T_{vj}=150^\circ C$	-	59.2	-		
SC data	Short-circuit current	$V_{CC}=800V, V_{GE}\leq 15V, T_{vj}=25^\circ C$ $V_{CES}\leq 1200V, t_p\leq 10\mu s$	-	2478	-	A	
R_{thJC}	Thermal resistance, junction to case	per IGBT	-	0.058	-	K/W	
R_{thCH}	Thermal resistance, case to heatsink	per IGBT/ $\lambda_{grease}=1W/(m\cdot K)$	-	0.074	-	K/W	
T_{vjop}	Temperature under switching conditions		-40		150	$^\circ C$	

Diode, Inverter

Maximum Rated Values

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^\circ C$	1200	V
I_F	Forward current, DC	$T_C=100^\circ C, T_{vj}=150^\circ C$	450	A
I_{FRM}	Repetitive peak forward current	$t_p=1ms$	900	A
I^2t	I^2t -value	$V_R=0V, t_p=10ms, T_{vj}=150^\circ C$	-	A^2s

Characteristic Values

V_F	Continuous forward voltage	$I_F=450A$ $V_{GE}=0V$	$T_{vj}=25^\circ C$	-	2.44	-	V
			$T_{vj}=125^\circ C$	-	2.08	-	
			$T_{vj}=150^\circ C$	-	2.00	-	
I_{RM}	Peak reverse recovery current	$V_R=600V$ $I_F=450A$	$T_{vj}=25^\circ C$	-	153	-	A
			$T_{vj}=125^\circ C$	-	264	-	
			$T_{vj}=150^\circ C$	-	298	-	
t_{rr}	Reverse recovery time		$T_{vj}=25^\circ C$	-	167	-	ns
			$T_{vj}=125^\circ C$	-	616	-	
			$T_{vj}=150^\circ C$	-	671	-	
Q_r	Recovered charge	$T_{vj}=25^\circ C$	-	21.5	-	μC	
		$T_{vj}=125^\circ C$	-	68.0	-		
		$T_{vj}=150^\circ C$	-	84.9	-		

E _{rec}	Reverse recovery energy		T _{vj} =25°C	-	8.33	-	mJ
			T _{vj} =125°C	-	24.8	-	
			T _{vj} =150°C	-	31.7	-	
R _{thJC}	Thermal resistance, junction to case	per diode	-	0.1	-	K/W	
R _{thCH}	Thermal resistance, case to heatsink	per diode/ λgrease=1W/(m·K)	-	0.049	-	K/W	
T _{vjop}	Temperature under switching conditions		-40		150	°C	

NTC Thermistor Characteristics

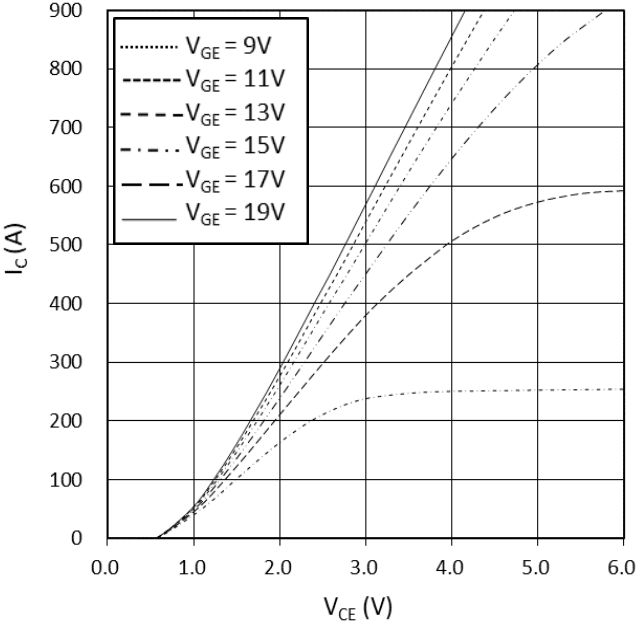
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
R ₂₅	Rated resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of resistance	T _C =100°C, R ₁₀₀ =493Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-constant	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$	-	3375	-	K
B _{25/80}	B-constant	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15K))]$	-	3411	-	
B _{25/100}	B-constant	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15K))]$	-	3433	-	

Module

Symbol	Item	Conditions	Rating			Unit
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS, f=50Hz, t=1min	4000			V
-	Material of module baseplate	-	Cu			-
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al ₂ O ₃			-
T _{stg}	Storage temperature	-	-40~125			°C
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
M	Mounting torque for module mounting	Screw M6	3.0	-	5.0	Nm
	Terminal connection torque	Screw M6	2.5	-	5.0	Nm
ds	Creepage distance	Terminal to terminal	-	13	-	mm
		Terminal to base plate	-	14.5	-	
da	Clearance	Terminal to terminal	-	10	-	mm
		Terminal to base plate	-	12.5	-	
m	Weight	-	-	346	-	g

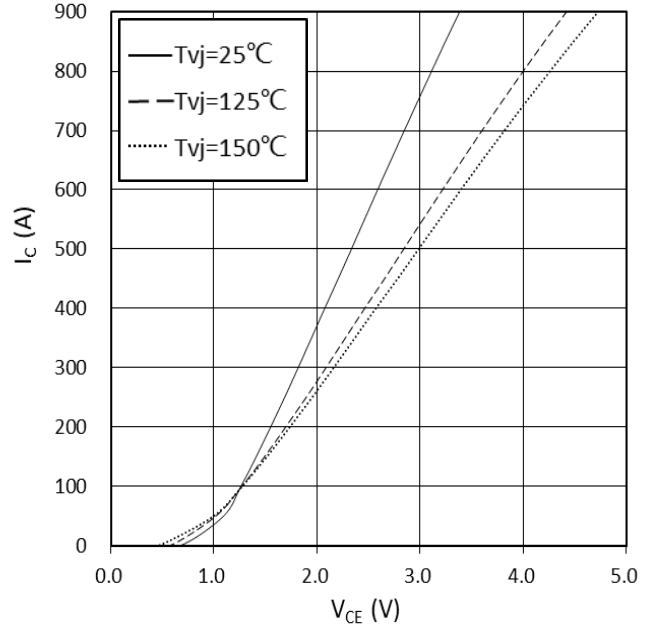
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



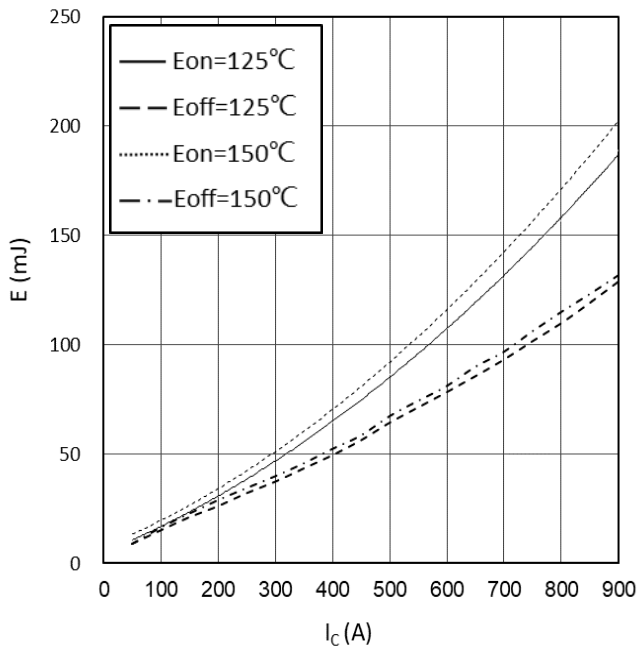
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



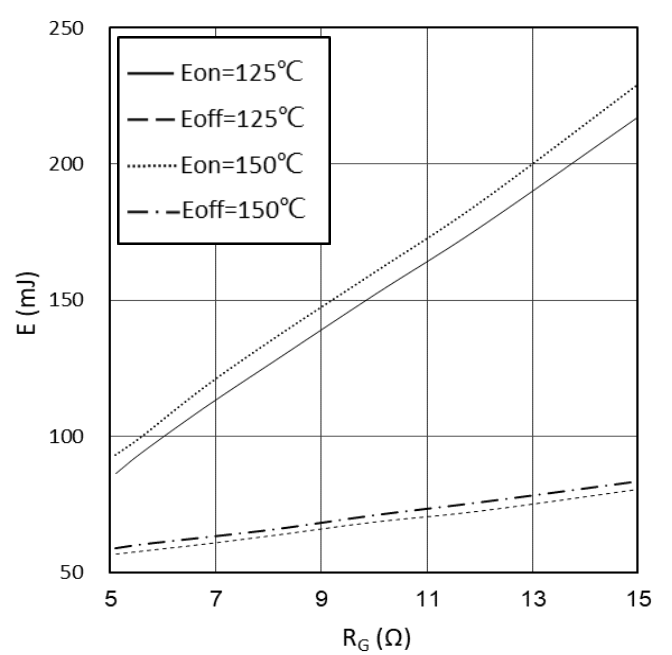
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{V}$, $R_{Gon} = 5.1\Omega$, $R_{Goff} = 5.1\Omega$, $V_{CE} = 600\text{V}$



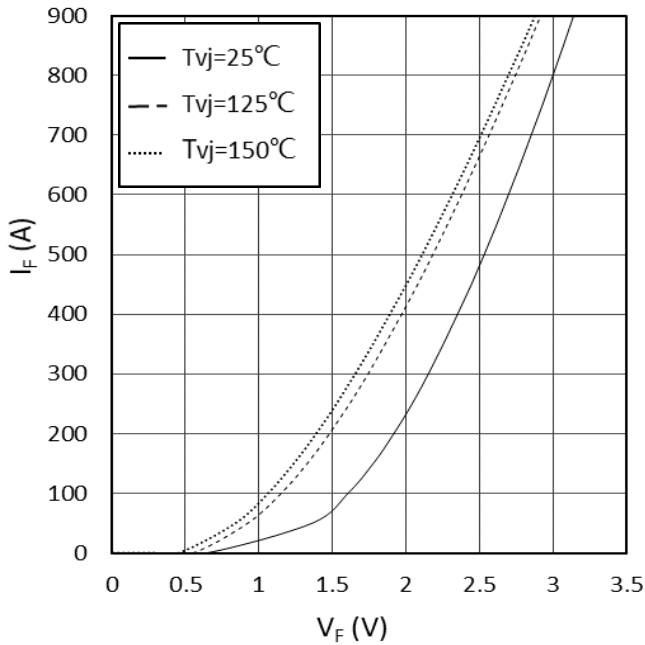
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{V}$, $I_C = 600\text{A}$, $V_{CE} = 600\text{V}$



forward characteristic of Diode, Inverter (typical)

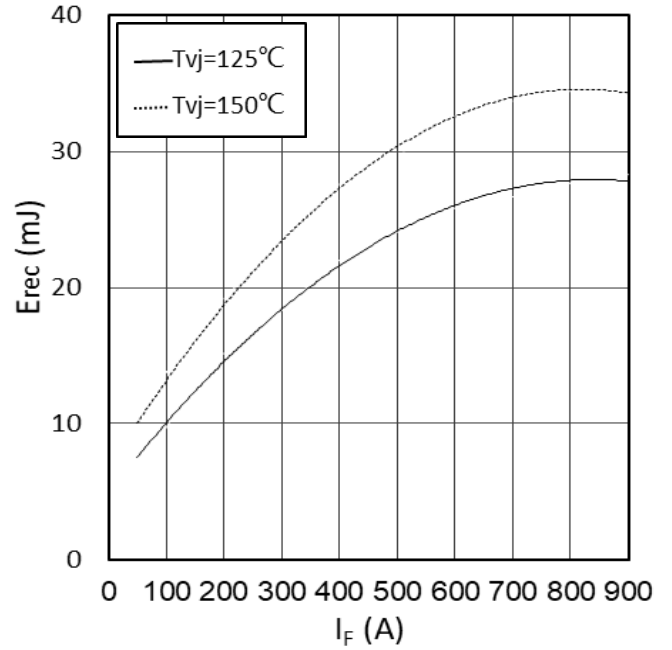
$I_F = f(V_F)$



switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$

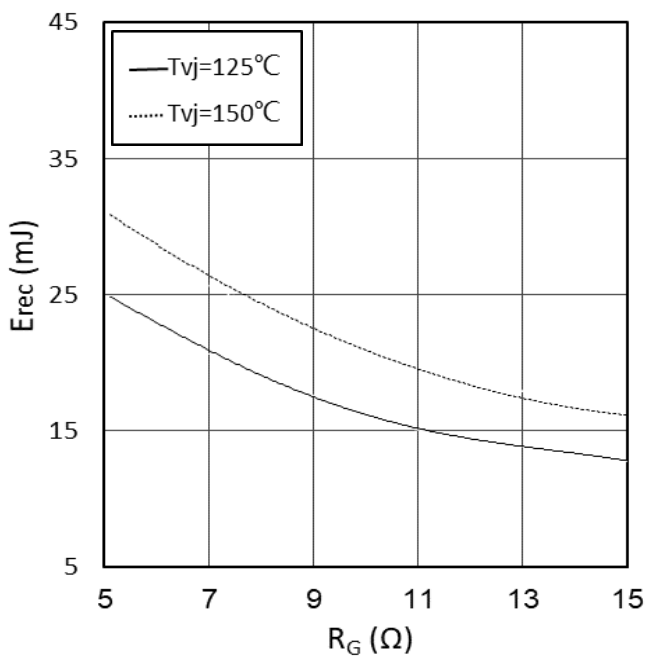
$R_{Gon}=5.1\Omega, V_{CE}=600V$



switching losses Diode, Inverter (typical)

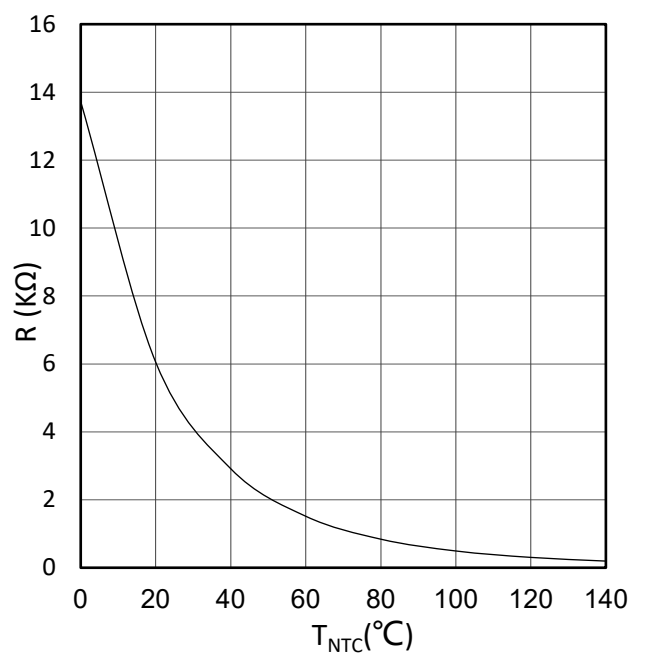
$E_{rec} = f(R_G)$

$I_F=600A, V_{CE}=600V$



NTC-Thermistor-temperature characteristic(typical)

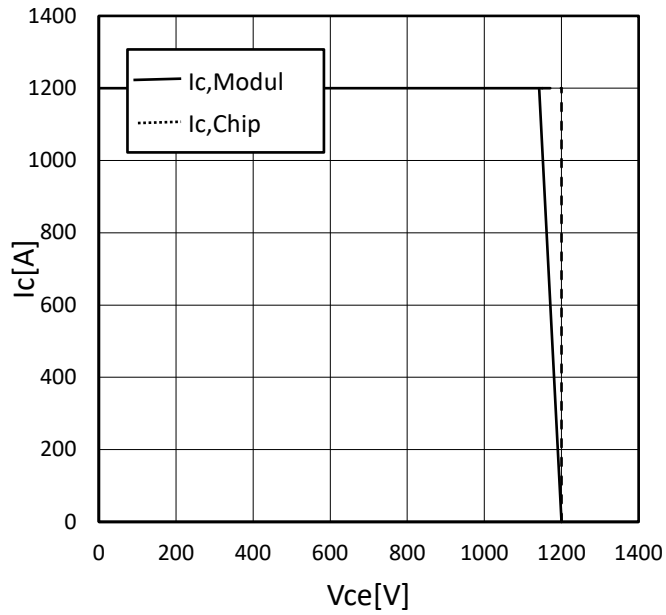
$R=f(T)$



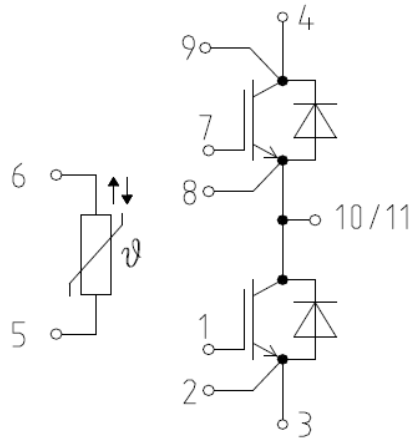
reverse bias safe operating area IGBT,Inverter (RBSOA)

$I_C = f(V_{CE})$

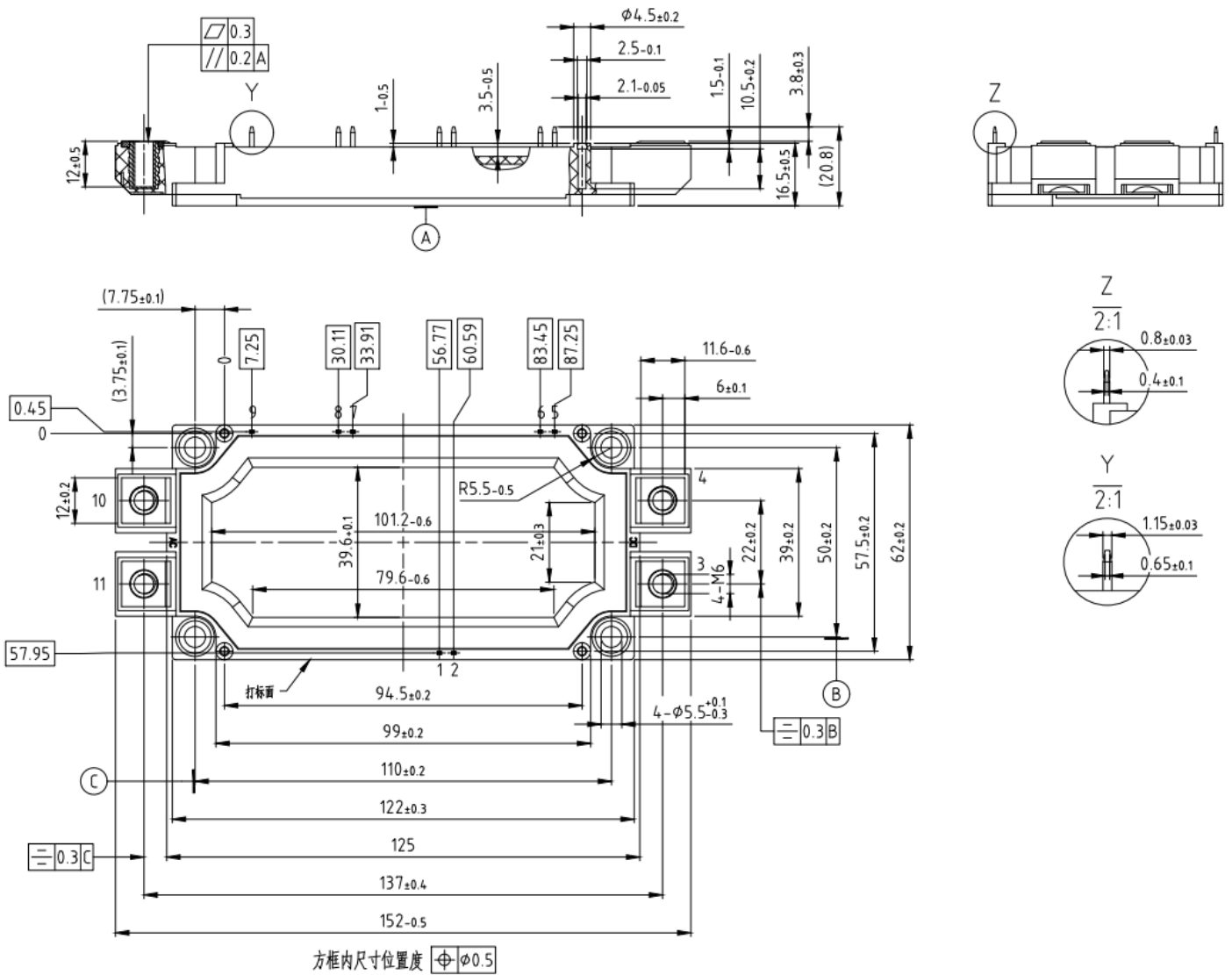
$V_{GE} = \pm 15V, R_{Gon} = 5.1\Omega, R_{Goff} = 5.1\Omega, T_{vj} = 25^\circ C$



Circuit diagram headline



Package outlines (Unit: mm)



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序号 Item	日期 Date	变更记录及描述 Change History Description	版本序号 Rev. item	经办人 Responsibility
1	2023.3.1	初版规格书发布，版本为V1.0	2023 3 Ver1.0	梁华文
2	2023.3.31	更新曲线，变更为V1.1版本	2023 3 Ver1.1	梁华文
3	2023.10.19	更新外形图，变更为V1.2版本	2023 10 Ver1.2	梁华文